
CSE477 VLSI Digital Circuits Fall 2002

Lecture 11: Designing for Speed

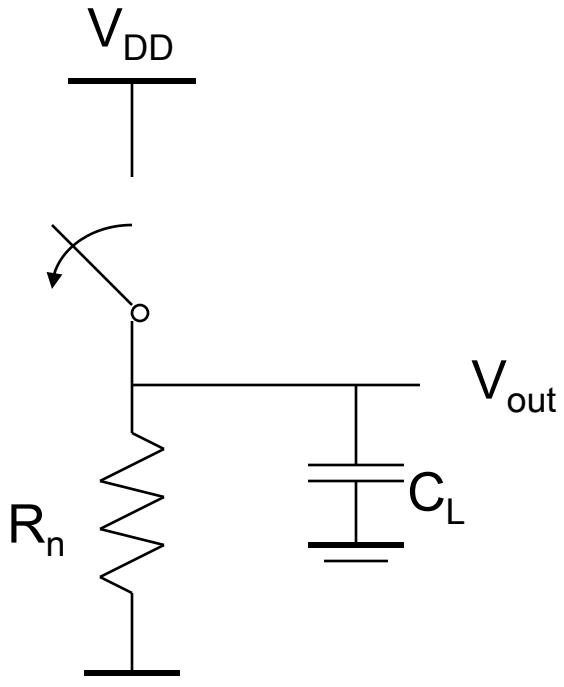
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[Adapted from Rabaey's *Digital Integrated Circuits*, ©2002, J. Rabaey et al.]

Cray was a legend in computers ... said that he liked to hire inexperienced engineers right out of school, because they do not usually know what's supposed to be impossible.

The Soul of a New Machine, Kidder, pg. 77

Review: CMOS Inverter: Dynamic



$$V_{in} = V_{DD}$$

$$t_{pHL} = f(R_n, C_L)$$

$$t_{pHL} = 0.69 R_{eqn} C_L$$

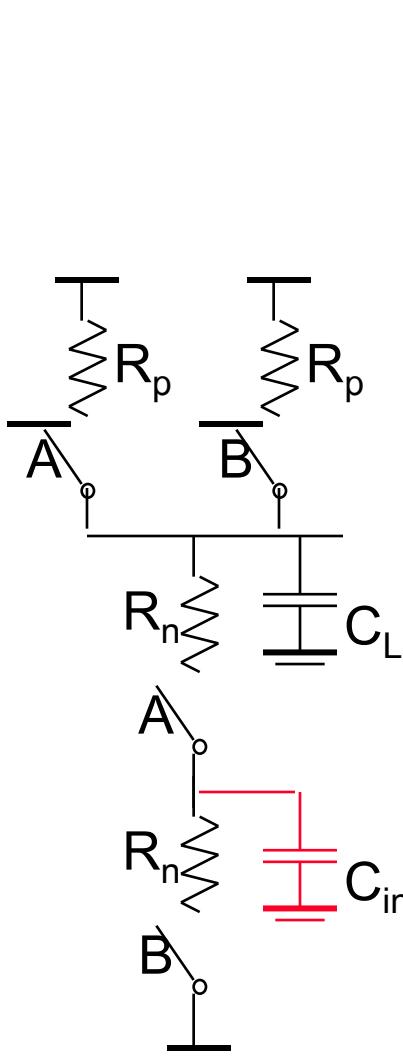
$$t_{pHL} = 0.69 \left(\frac{3}{4} (C_L V_{DD}) / I_{DSATn} \right)$$

$$= 0.52 C_L / (W/L_n k' n V_{DSATn})$$

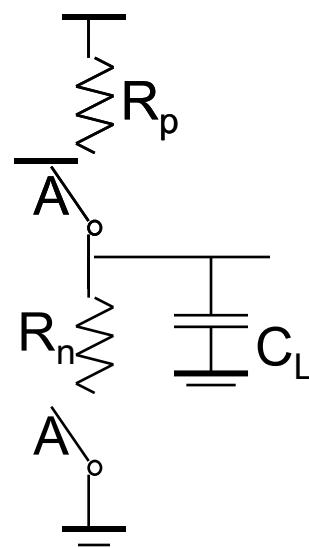
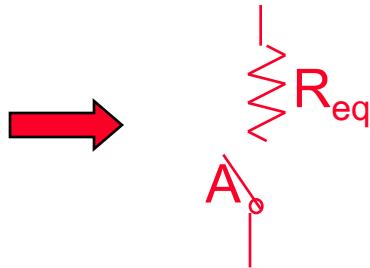
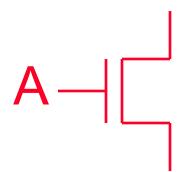
Review: Designing Inverters for Performance

- Reduce C_L
 - internal diffusion capacitance of the gate itself
 - interconnect capacitance
 - fanout
- Increase W/L ratio of the transistor
 - the most powerful and effective performance optimization tool in the hands of the designer
 - watch out for self-loading!
- Increase V_{DD}
 - only minimal improvement in performance at the cost of increased energy dissipation
- Slope engineering - keeping signal rise and fall times smaller than or equal to the gate propagation delays and of approximately equal values
 - good for performance
 - good for power consumption

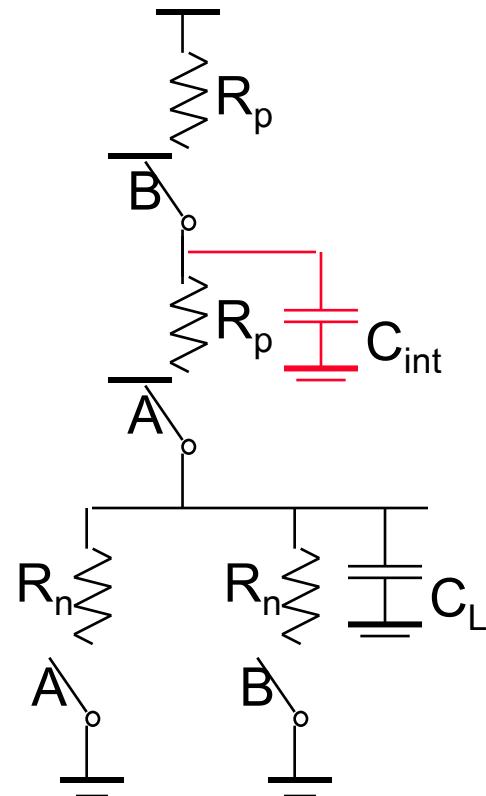
Switch Delay Model



NAND



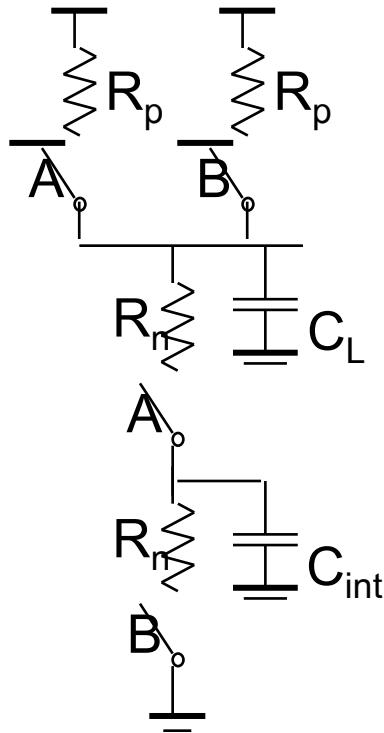
INVERTER



NOR

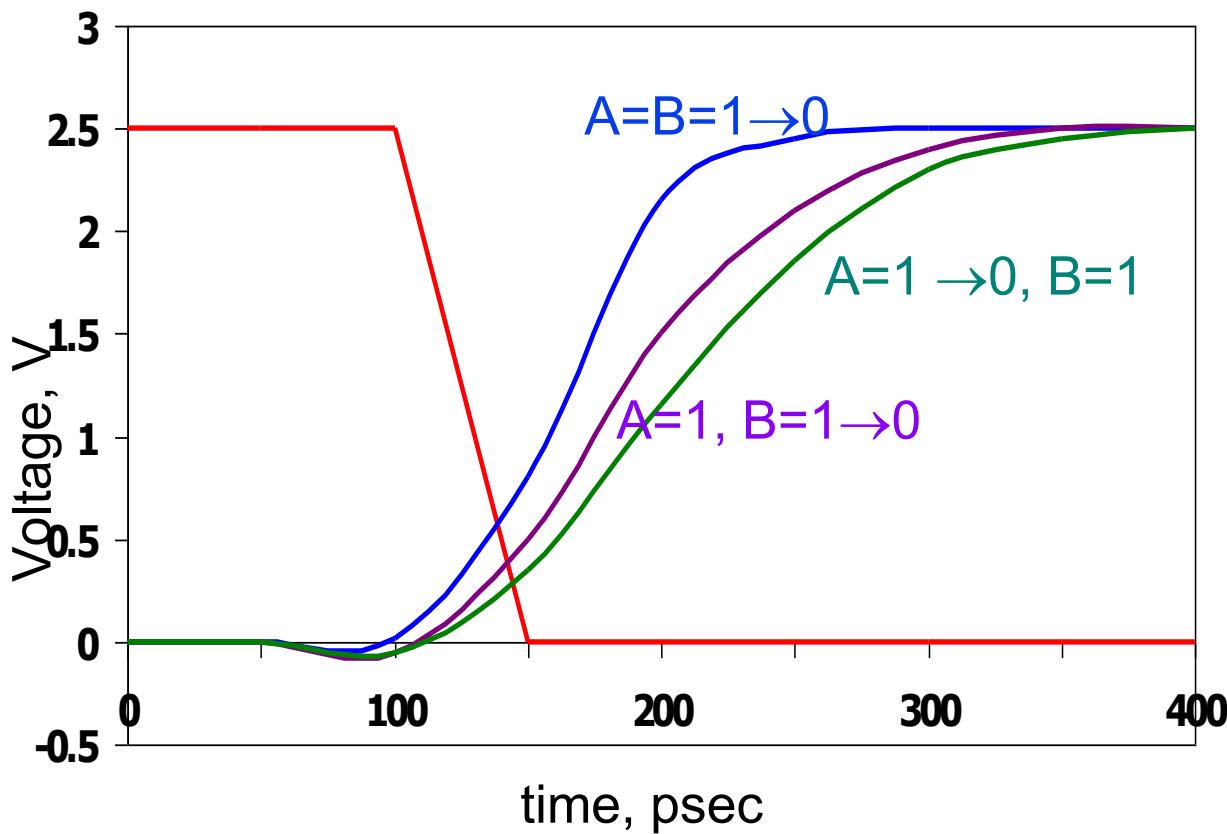
Input Pattern Effects on Delay

- Delay is dependent on the **pattern** of inputs



- Low to high transition
 - both inputs go low
 - delay is $0.69 R_p / 2 C_L$ since two p-resistors are on in parallel
 - one input goes low
 - delay is $0.69 R_p C_L$
- High to low transition
 - both inputs go high
 - delay is $0.69 2R_n C_L$
- Adding transistors in series (without sizing) slows down the circuit

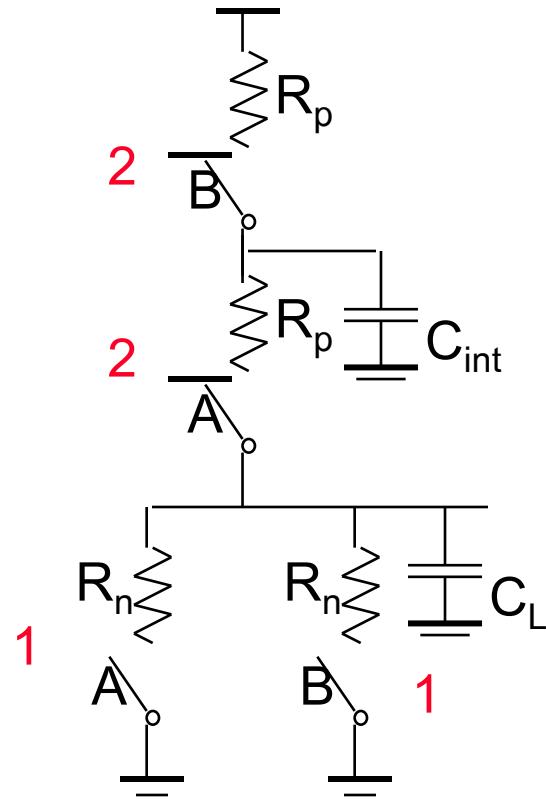
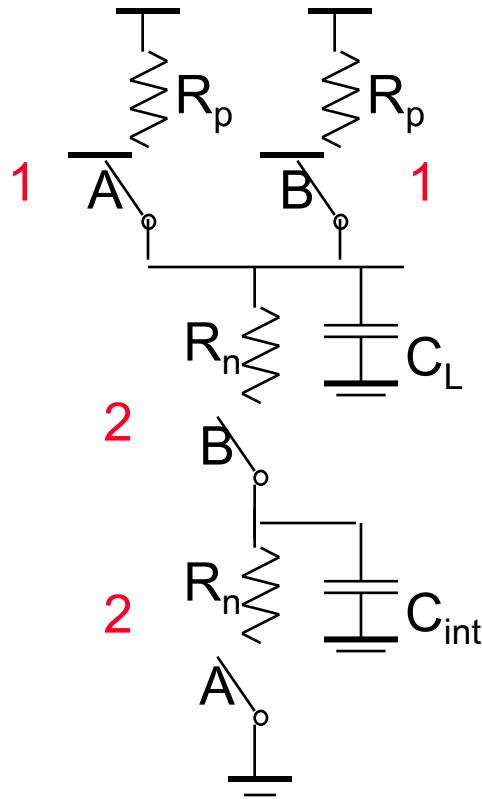
Delay Dependence on Input Patterns



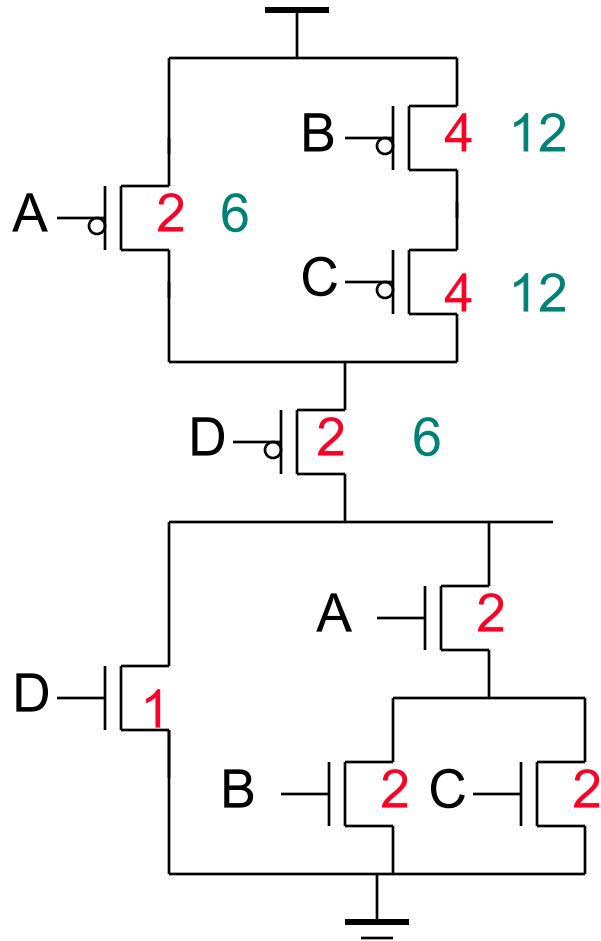
2-input NAND with
NMOS = $0.5\mu\text{m}/0.25\mu\text{m}$
PMOS = $0.75\mu\text{m}/0.25\mu\text{m}$
 $C_L = 10 \text{ fF}$

| Input Data Pattern | Delay (psec) |
|--------------------------|--------------|
| $A=B=0 \rightarrow 1$ | 69 |
| $A=1, B=0 \rightarrow 1$ | 62 |
| $A=0 \rightarrow 1, B=1$ | 50 |
| $A=B=1 \rightarrow 0$ | 35 |
| $A=1, B=1 \rightarrow 0$ | 76 |
| $A=1 \rightarrow 0, B=1$ | 57 |

Transistor Sizing

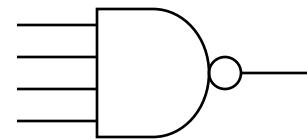
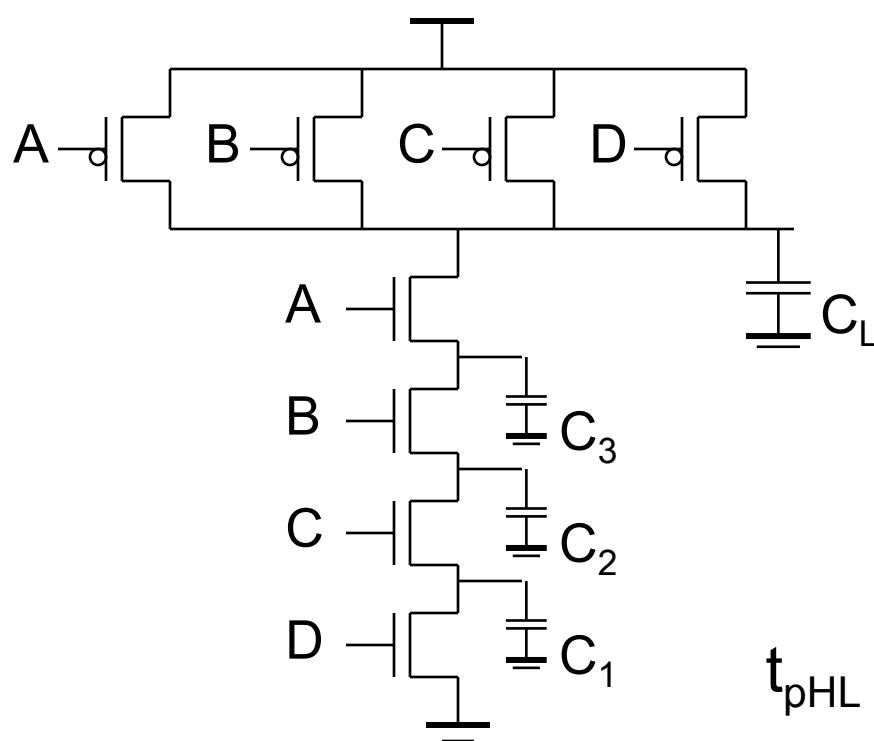


Transistor Sizing a Complex CMOS Gate



$$\text{OUT} = !(D + A \cdot (B + C))$$

Fan-In Considerations

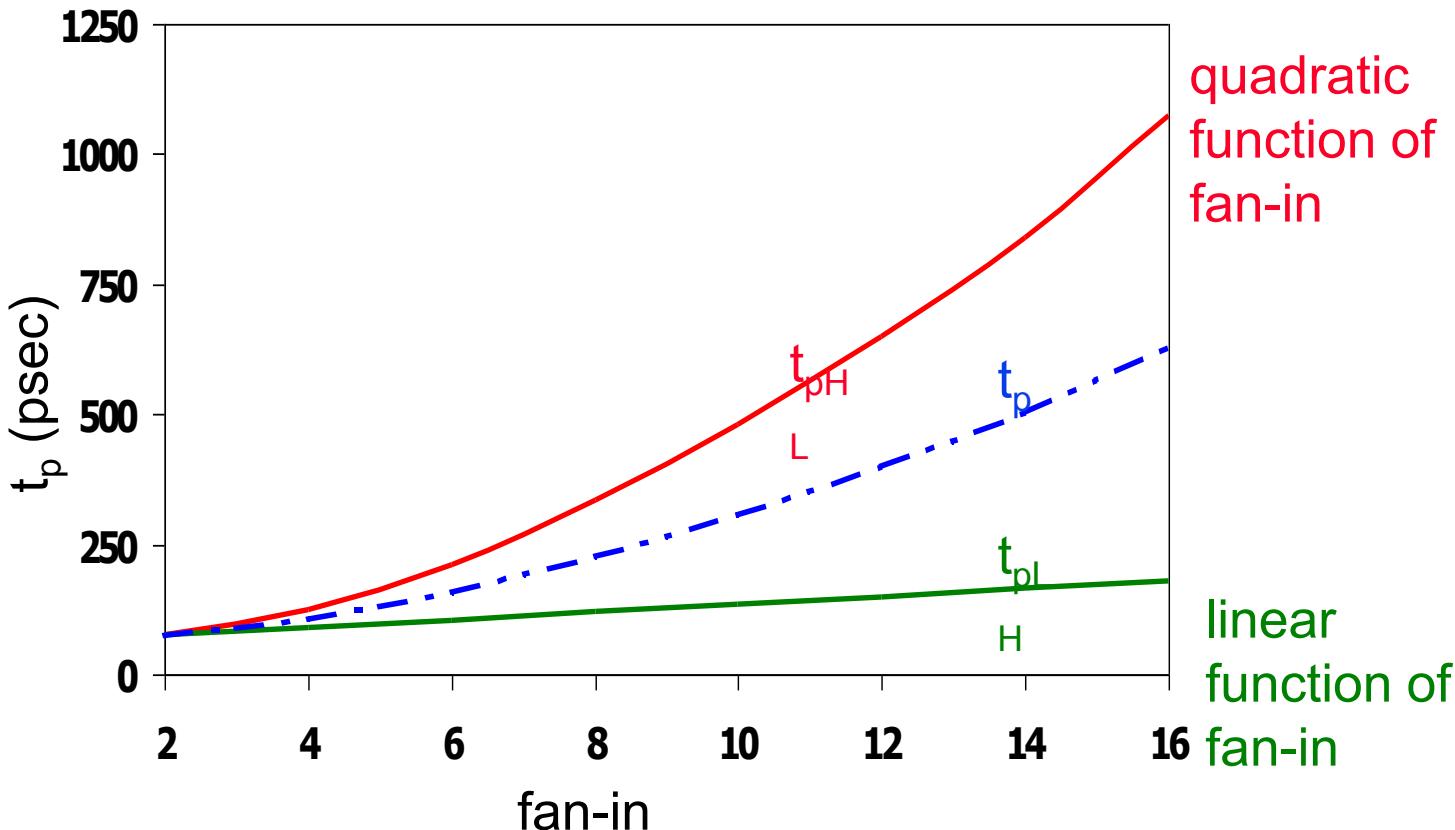


Distributed RC model
(Elmore delay)

$$t_{pHL} = 0.69 R_{eqn}(C_1 + 2C_2 + 3C_3 + 4C_L)$$

Propagation delay deteriorates rapidly as a function of fan-in – **quadratically** in the worst case.

t_p as a Function of Fan-In



- ❑ Gates with a fan-in greater than 4 should be avoided.

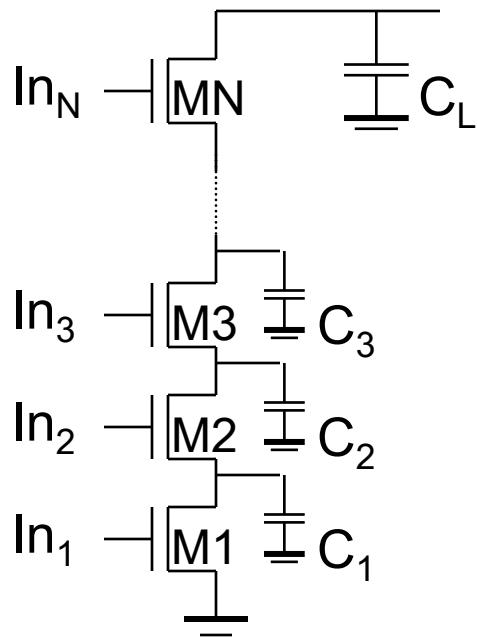
Fast Complex Gates: Design Technique 1

- ❑ Transistor sizing

- as long as fan-out capacitance dominates

- ❑ Progressive sizing

Distributed RC line



$M1 > M2 > M3 > \dots > MN$

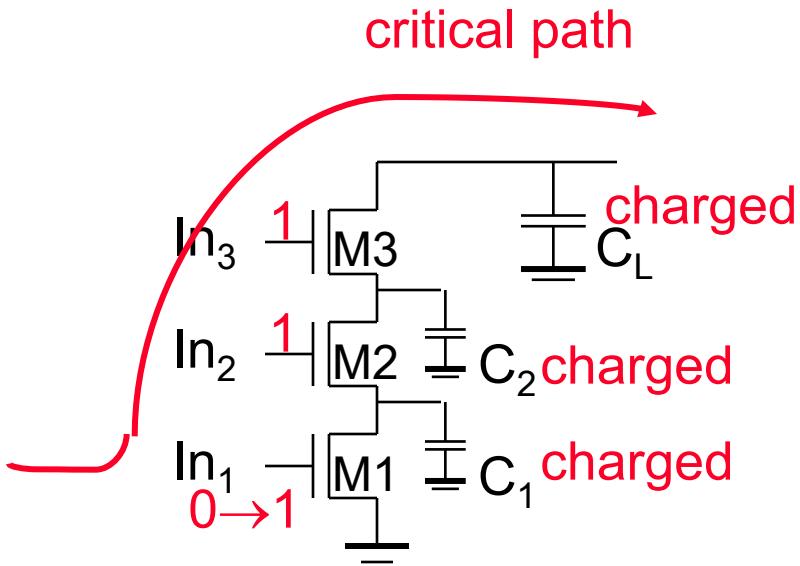
(the fet closest to the **output** should be the smallest)

Can reduce delay by more than 20%; decreasing gains as technology shrinks

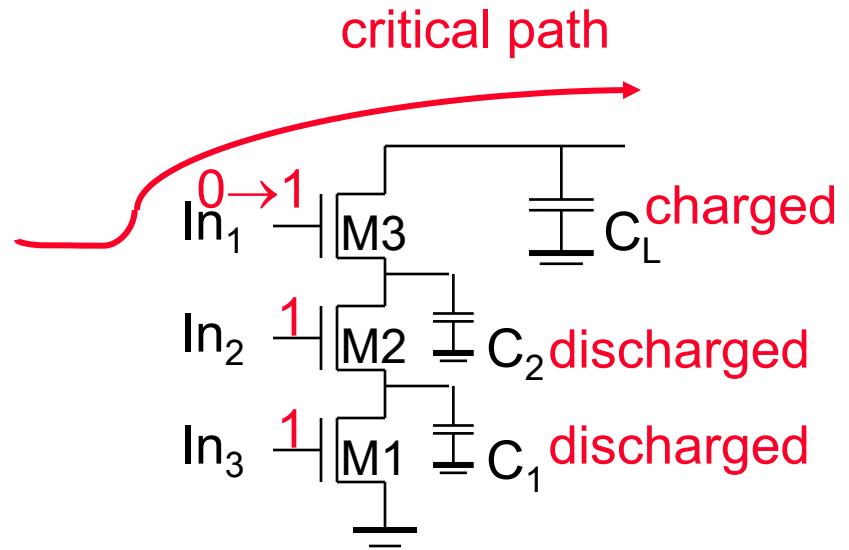
Fast Complex Gates: Design Technique 2

□ Input re-ordering

- when not all inputs arrive at the same time

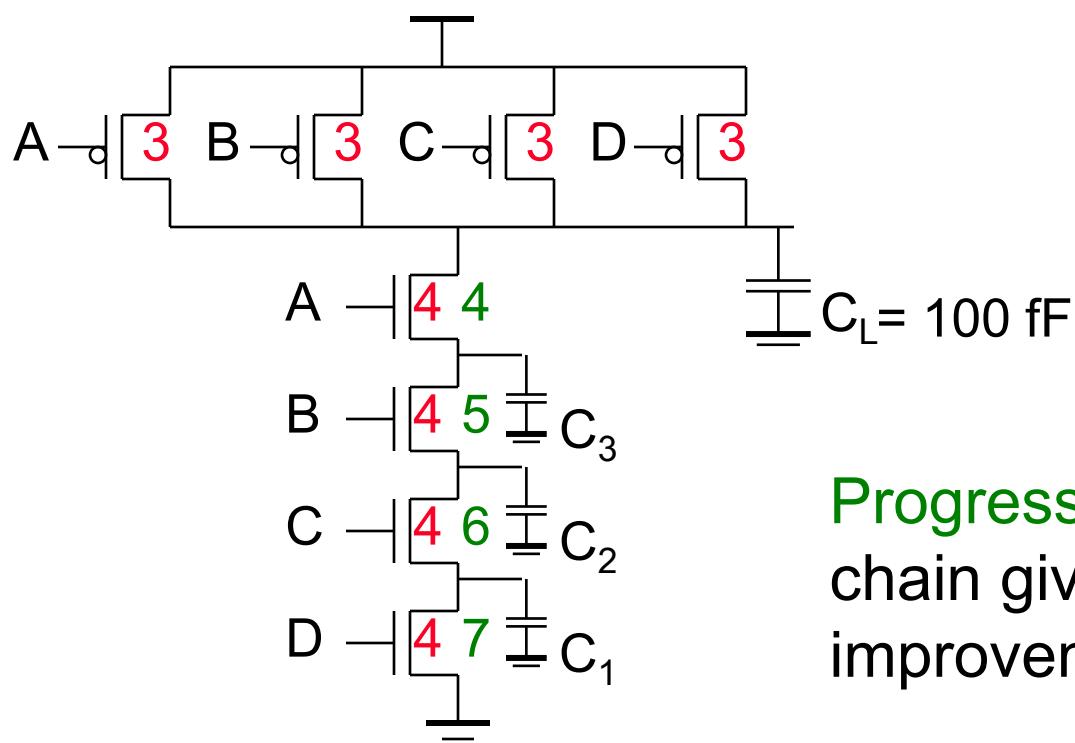


delay determined by time to discharge C_L , C_1 and C_2



delay determined by time to discharge C_L

Sizing and Ordering Effects



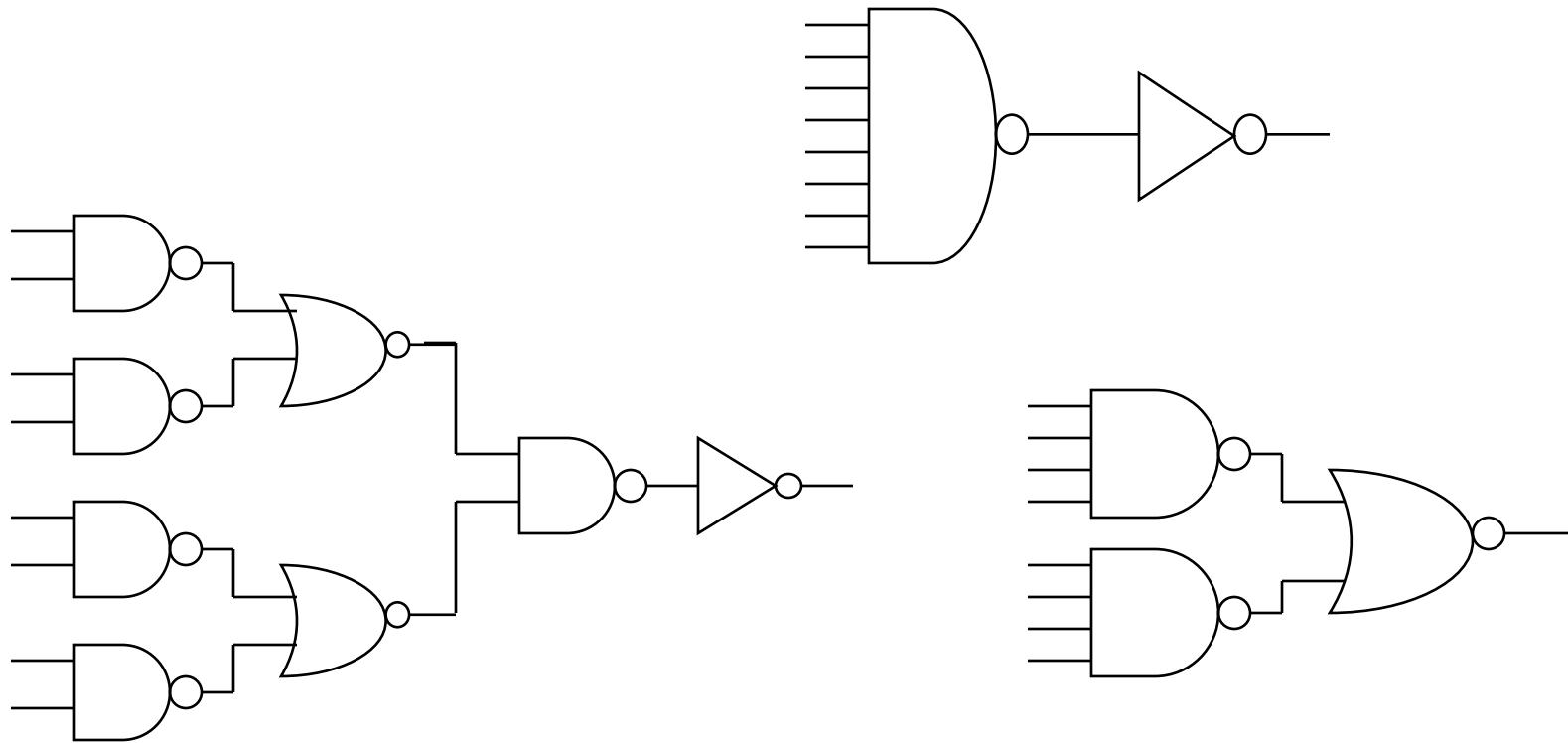
Progressive sizing in pull-down chain gives up to a 23% improvement.

Input ordering saves 5%
critical path A – 23%
critical path D – 17%

Fast Complex Gates: Design Technique 3

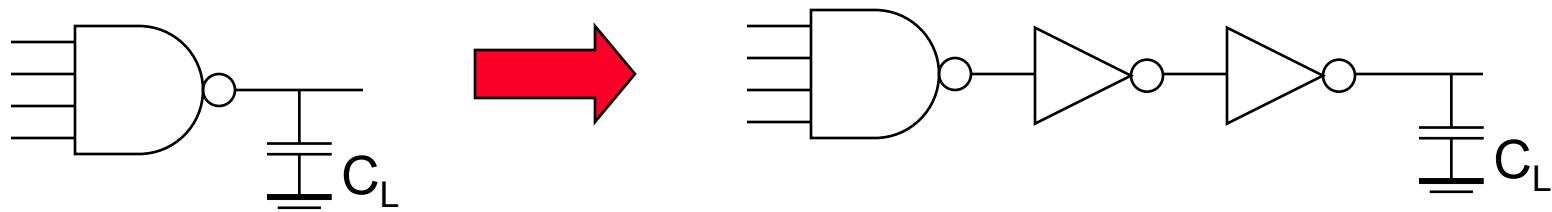
- ❑ Alternative logic structures

$$F = ABCDEFGH$$



Fast Complex Gates: Design Technique 4

- ❑ Isolating fan-in from fan-out using buffer insertion



- ❑ Real lesson is that optimizing the propagation delay of a gate in isolation is misguided.

Fast Networks: Design Technique 5 - Logical Effort

The optimum fan-out for a chain of N inverters driving a load C_L is

$$f = \sqrt[N]{C_L/C_{in}}$$

- so, if we can, keep the fan-out per stage around 4.
- Can the same approach (**logical effort**) be used for any combinational circuit?
 - For a complex gate, we expand the inverter equation

$$t_p = t_{p0} (1 + C_{ext}/\gamma C_g) = t_{p0} (1 + f/\gamma)$$

to

$$t_p = t_{p0} (p + g f/\gamma)$$

- t_{p0} is the intrinsic delay of an inverter
- f is the effective fan-out (C_{ext}/C_g) – also called the **electrical effort**
- p is the ratio of the intrinsic (unloaded) delay of the complex gate and a simple inverter (a function of the gate topology and layout style)
- g is the **logical effort**

Intrinsic Delay Term, p

- ❑ The more involved the structure of the complex gate, the higher the intrinsic delay compared to an inverter

| Gate Type | p |
|--------------|-------------------|
| Inverter | 1 |
| n-input NAND | n |
| n-input NOR | n |
| n-way mux | 2n |
| XOR, XNOR | $n \cdot 2^{n-1}$ |

Ignoring second order effects such as internal node capacitances

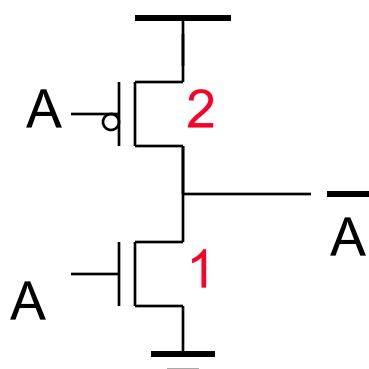
Logical Effort Term, g

- ❑ g represents the fact that, for a given load, complex gates have to work harder than an inverter to produce a similar (speed) response
 - the logical effort of a gate tells how much worse it is at producing an output current than an inverter (how much more input capacitance a gate presents to deliver it same output current)

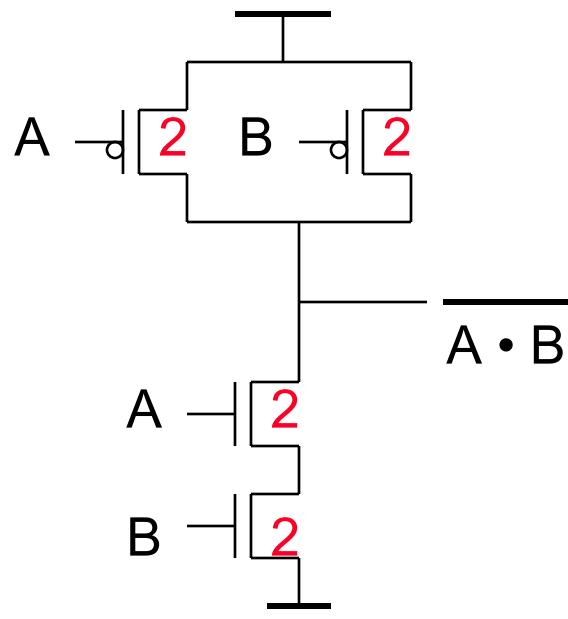
| Gate Type | g (for 1 to 4 input gates) | | | |
|-----------|----------------------------|-----|-----|----------|
| | 1 | 2 | 3 | 4 |
| Inverter | 1 | | | |
| NAND | | 4/3 | 5/3 | (n+2)/3 |
| NOR | | 5/3 | 7/3 | (2n+1)/3 |
| mux | | 2 | 2 | 2 |
| XOR | | 4 | 12 | |

Example of Logical Effort

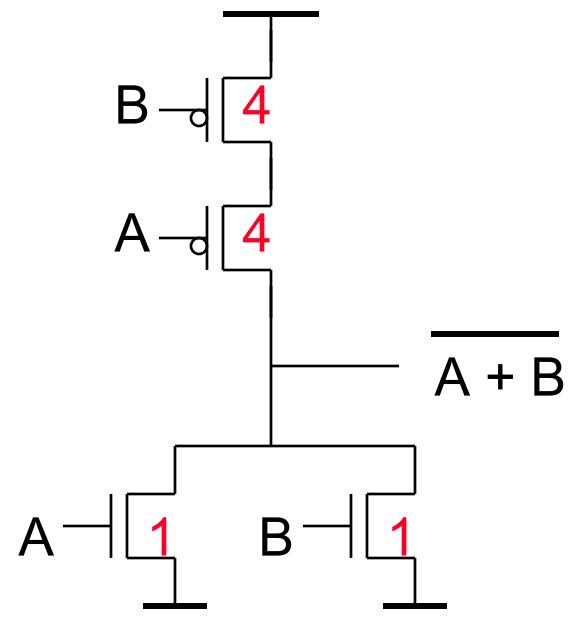
- Assuming a pmos/nmos ratio of 2, the input capacitance of a minimum-sized inverter is three times the gate capacitance of a minimum-sized nmos (C_{unit})



$$C_{unit} = 3$$

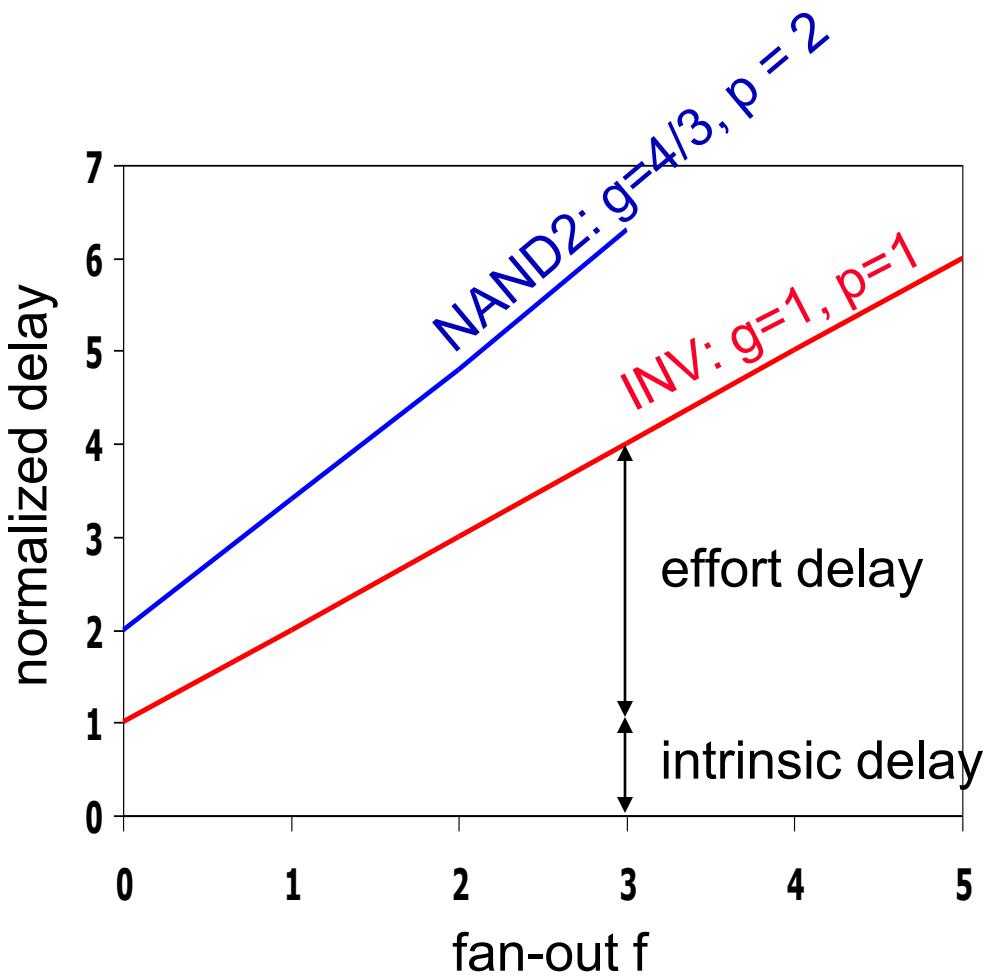


$$C_{unit} = 4$$



$$C_{unit} = 5$$

Delay as a Function of Fan-Out



- ❑ The slope of the line is the logical effort of the gate
- ❑ The y-axis intercept is the intrinsic delay
- ❑ Can adjust the delay by adjusting the effective fan-out (by sizing) or by choosing a gate with a different logical effort
- ❑ Gate effort: $h = fg$

Path Delay of Complex Logic Gate Network

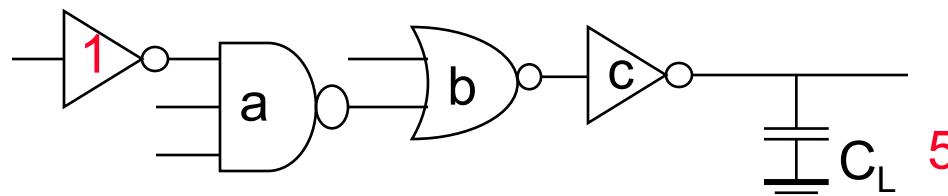
- ❑ Total path delay through a combinational logic block

$$t_p = \sum t_{p,j} = t_{p0} \sum (p_j + (f_j g_j) / \gamma)$$

- ❑ So, the minimum delay through the path determines that each stage should bear the same gate effort

$$f_1 g_1 = f_2 g_2 = \dots = f_N g_N$$

- ❑ Consider optimizing the delay through the logic network



how do we determine a, b, and c sizes?

Path Delay Equation Derivation

- ❑ The path logical effort, $G = \prod g_i$
- ❑ And the path effective fan-out (path electrical effort) is $F = C_L/g_1$
- ❑ The branching effort accounts for fan-out to other gates in the network

$$b = (C_{\text{on-path}} + C_{\text{off-path}})/C_{\text{on-path}}$$

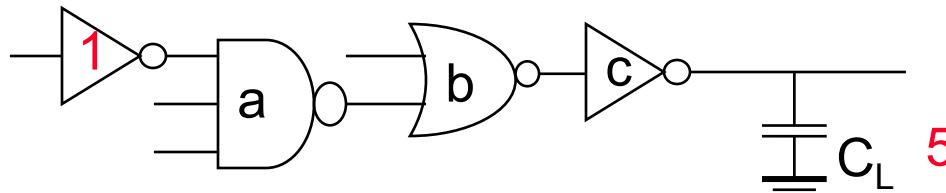
- ❑ The path branching effort is then $B = \prod b_i$
- ❑ And the total path effort is then $H = GFB$
- ❑ So, the minimum delay through the path is

$$D = t_{p0} \left(\sum p_j + (N \sqrt[N]{H})/\gamma \right)$$

Path Delay of Complex Logic Gates, con't

- For gate i in the chain, its size is determined by

$$s_i = (g_1 s_1) / g_i \prod_{j=1}^{i-1} (f_j/b_j)$$



- For this network

- $F = C_L/C_{g1} = 5$
 - $G = 1 \times 5/3 \times 5/3 \times 1 = 25/9$
 - $B = 1$ (no branching)
 - $H = GFB = 125/9$, so the optimal stage effort is $\sqrt[4]{H} = 1.93$
 - Fan-out factors are $f_1 = 1.93$, $f_2 = 1.93 \times 3/5 = 1.16$, $f_3 = 1.16$, $f_4 = 1.93$
 - So the gate sizes are $a = f_1 g_1 / g_2 = 1.16$, $b = f_1 f_2 g_1 / g_3 = 1.34$ and $c = f_1 f_2 f_3 g_1 / g_4 = 2.60$

Fast Complex Gates: Design Technique 6

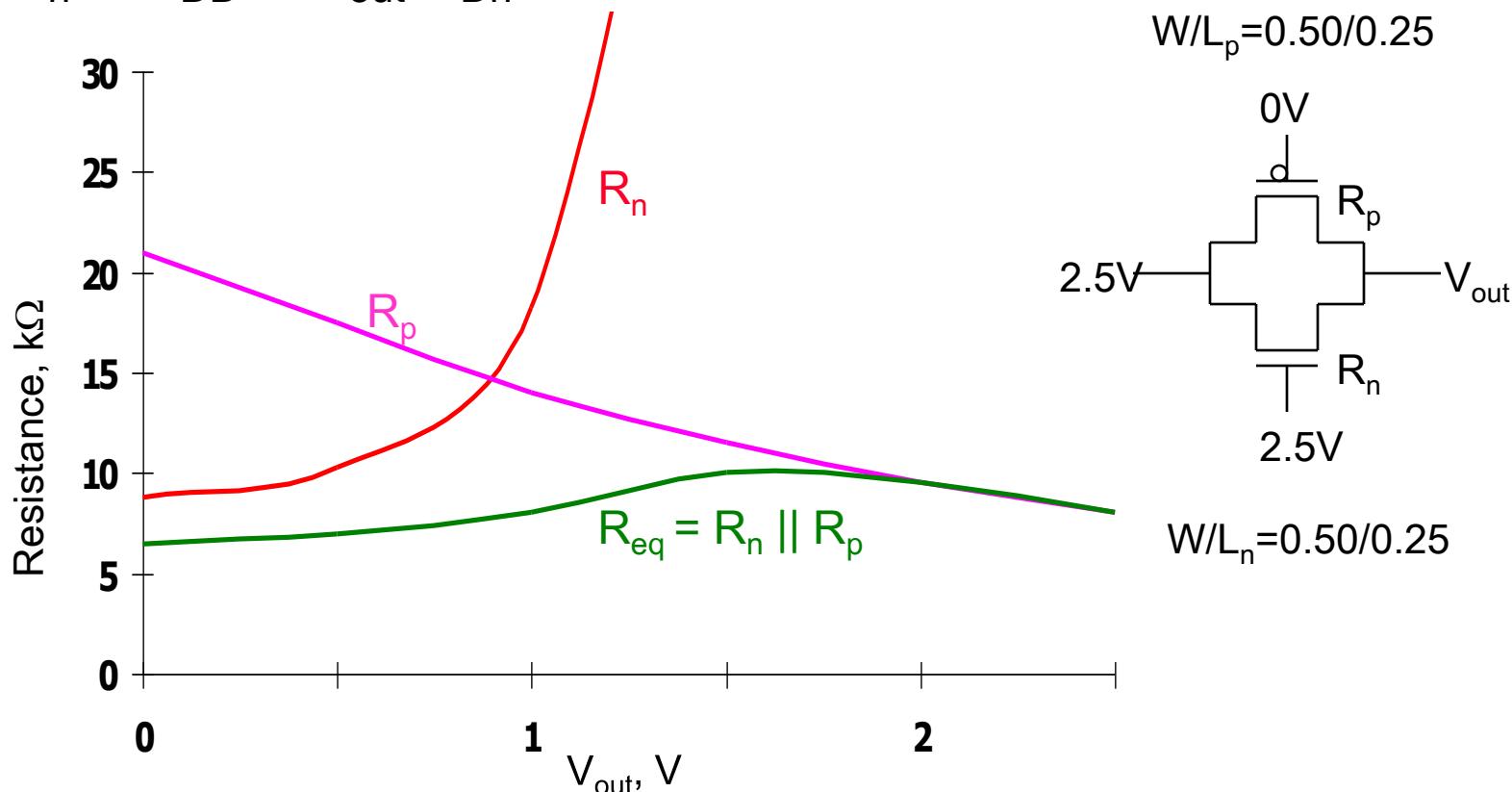
- Reducing the voltage swing

$$\begin{aligned} t_{pHL} &= 0.69 \left(\frac{3}{4} (C_L V_{DD}) / I_{DSATn} \right) \\ &= 0.69 \left(\frac{3}{4} (C_L V_{swing}) / I_{DSATn} \right) \end{aligned}$$

- linear reduction in delay
- also reduces power consumption
- requires use of “sense amplifiers” on the receiving end to restore the signal level (will look at their design when covering memory design)

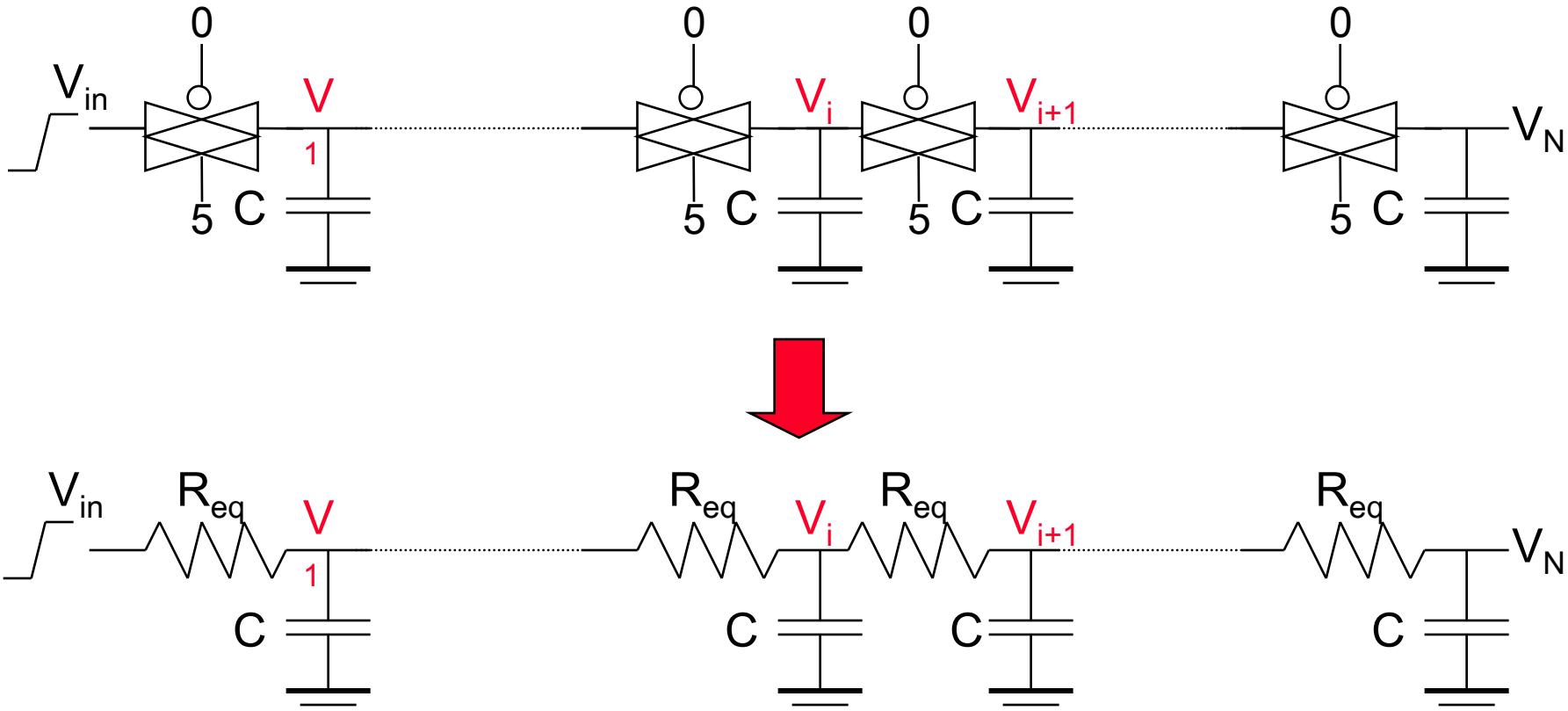
TG Logic Performance

- ❑ Effective resistance of the TG is modeled as a parallel connection of R_p ($= (V_{DD} - V_{out}) / (-I_{Dp})$) and R_n ($= V_{DD} - V_{out} / |I_{Dn}|$)



- ❑ So, the assumption that the TG switch has a constant resistive value, R_{eq} , is acceptable

Delay of a TG Chain

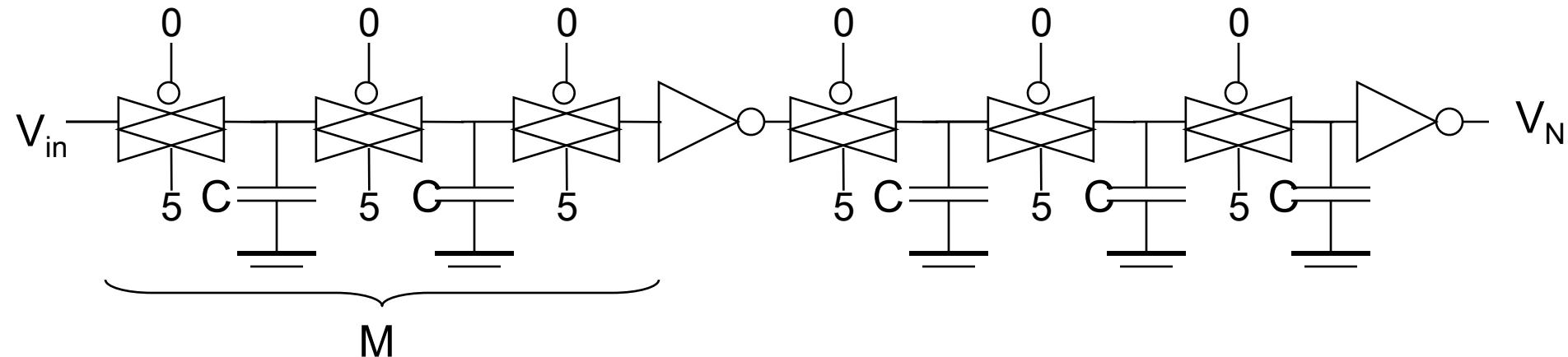


□ Delay of the RC chain (N TG's in series) is

$$t_p(V_n) = 0.69 \sum_{k=1}^N k C R_{eq} = 0.69 C R_{eq} (N(N+1))/2 \approx 0.35 C R_{eq} N^2$$

TG Delay Optimization

- ❑ Can speed it up by inserting buffers every M switches



- ❑ Delay of buffered chain (M TG's between buffer)

$$t_p = 0.69 \lfloor N/M \text{ CR}_{eq} (M(M+1))/2 \rfloor + (N/M - 1) t_{pbuf}$$

$$M_{opt} = 1.7 \sqrt{(t_{pbuf}/\text{CR}_{eq})} \approx 3 \text{ or } 4$$

Next Lecture and Reminders

❑ Next lecture

- ❑ Designing energy efficient logic
 - Reading assignment – Rabaey, et al, 5.5 & 6.2.1

❑ Reminders

- ❑ HW3 due Oct 10th (hand in to TA)
- ❑ Class cancelled on Oct 10th as make up for evening midterm
- ❑ I will be out of town Oct 10th through Oct 15th and Oct 18th through Oct 23rd, so office hours during those periods are cancelled
- ❑ We will have a guest lecturer on Oct 22nd
- ❑ Evening midterm exam scheduled
 - Wednesday, October 16th from 8:15 to 10:15pm in 260 Willard
 - Only one midterm conflict filed for so far